

Silicon NPN Power Transistors

2SC2579

DESCRIPTION

- With TO-3PN package
- High power dissipation
- High current capability

APPLICATIONS

- For audio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

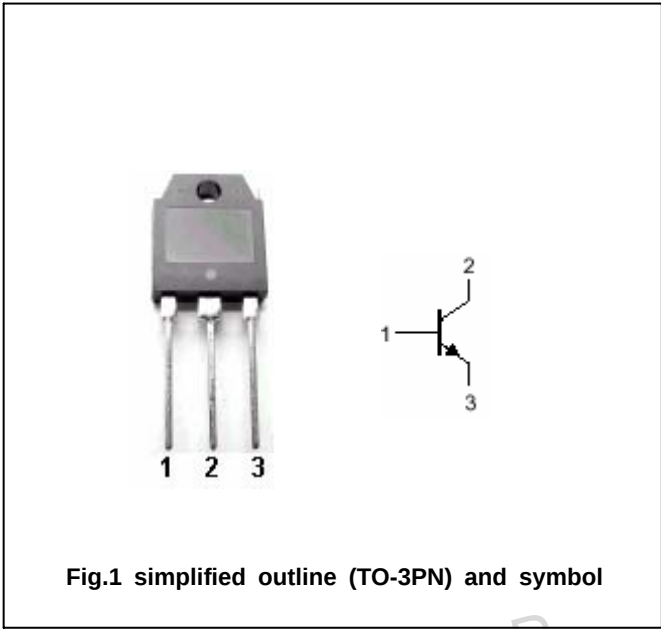


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	160	V
V_{CEO}	Collector-emitter voltage	Open base	160	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		8	A
P_C	Collector power dissipation	$T_C=25$	80	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

Silicon NPN Power Transistors

2SC2579

CHARACTERISTICS

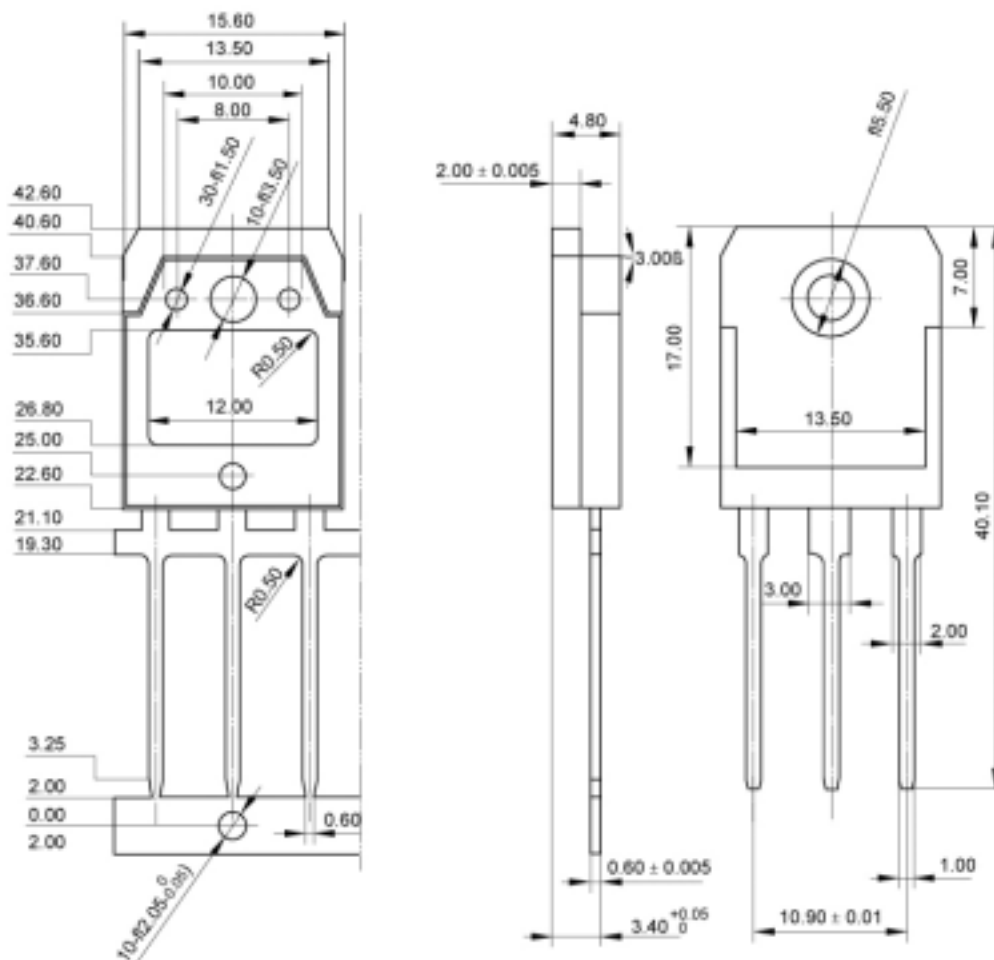
Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=5mA; I_E=0$	160			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA; R_{BE}=\infty$	160			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=5mA; I_C=0$	6			V
I_{CBO}	Collector cut-off current	$V_{CB}=160V; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=3A; V_{CE}=4V$	50			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=5A; I_B=0.5A$			2.0	V
f_T	Transition frequency	$I_C=0.5A; V_{CE}=10V$		20		MHz

Silicon NPN Power Transistors

2SC2579

PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)